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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Haupt Docket No.: INTECH 3.0-104
(2003 P 51718 US)
Serial No.: 10/766,053 Art Unit: 2822
Filed: January 28, 2004 Examiner: Thanh Y. Tran
Title: Method for N+ Doping of Amorphous Silicon and Polysilicon Electrodes in
Deep Trenches

Mail Stop: Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

RESPONSE

Dear Sir:

The following amendments and remarks are presented in response to the Examiner's
Office Action mailed January 10, 2006. Please enter the response and consider the remarks
below.

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Amendment